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GigaComm™ (SiGe) SPICE Modeling Kit



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APPLICATION NOTE

Objective

The objective of this kit is to provide sufficient circuit schematic and SPICE parameter information to perform system level interconnect modeling for devices in ON Semiconductor's high performance GigaComm (Silicon Germanium) logic family. The family has output edge rates as low as 20 ps and power supply levels of as low as 2.5 V. The kit is not intended to provide information necessary to perform circuit level modeling on the GigaComm (SiGe) devices.

Schematic Information

The kit contains representatives of input and output schematics, netlists, and waveform used for the GigaComm family devices. This application note will be modified as new devices are added. Table 1 describes the nomenclature used for modeling the schematic and netlist for GigaComm devices. The subcircuit models, such as input or output buffers, ESD and package simulate only device input or output paths. When used with interconnect models, a complete signal path may be modeled as shown in Figure 1.

Table 1. Schematics and Netlist Nomenclature

Parameter	Function Description		
V _{CC}	2.5/3.3 V for LVPECL and 0 V for LVECL		
V _{EE}	-2.5/-3.3 V for LVPECL and 0 V for LVECL		
V _{BB} or V _{MM}	Output Voltage Reference (See Device Data Sheet)		
V _{CS}	Internally Generated Voltage (≈ V _{EE} + 1.1 V ± 50 mV)*		
GND	Ground 0 V		
IN	True Input to CKT		
INB	Inverted Input to CKT		
Q	True Output of CKT		
QB	Inverted Output of CKT		

^{*}Note that the NBSG16VS, NBSG53A, NBSG72A, and NBSG86A are using V_{CS} to modulate the output amplitude (see device specifics for more details).

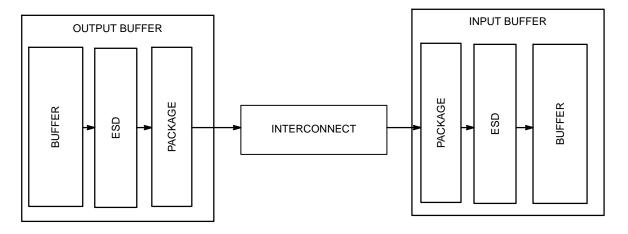


Figure 1. Interconnect Model Template

For device modeling, the behavioral LOGIC or gate functionality is not modeled (see Figure 2. DEVICE Model Template)

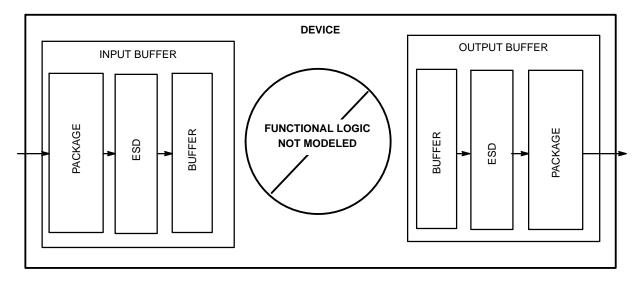


Figure 2. DEVICE Model Template

Package

A worst–case model is included to improve the accuracy of the system model. The package model represents the parasitics as they are measured a sizable distance from an AC ground pin. The package models should be placed on all external inputs to an input model, all external outputs for an output model and the V_{CC} line. Since the current in the V_{EE} pin is a constant, a package model for V_{EE} pin is not necessary. Please note that an internal V_{CS} voltage does not require a package model.

To shorten and speed up the simulation process, the simplified package model should be used. The input and output buffers schematic include the simplified QFN package model (Figures 4, 5, and 8).

Input Buffer

The "SG_INBUF" schematic and netlist are representing the input structures of devices for GigaComm family devices. The schematics require the addition of ESD and package models to be accurate; but are otherwise functionally correct. It is unnecessary to include an ESD or Package model for the V_{BB} or V_{MM} type pins of the models because V_{BB} type input is intended as an internal node for most applications. If a V_{BB} type input is modeled as an external node it is usually bypassed because it is a constant voltage, and adding ESD and Package parameters provide no additional benefit.

Output Buffer

Two output buffer schematics and netlists are modeled and can be seen on pages 6 and 8. The package models with all parasitics should be added for better accuracy. Any input or output that is driving or being driven by an off chip signal should include the ESD and package models. Open or floating pins will not require any ESD or package models. The output buffer models typically show internal differential inputs and outputs and should always be simulated with both output lines terminated, even when only one line or single ended use is intended. This will balance the output buffer's load.

Example of the Typical Interconnect Circuit

The output signal buffer SG_0BUF_01 with the ESD protection structure and the simplified package model properly terminated, driving the simplified input structure is shown in the Figure 13. The circuit provides working schematics of complete interconnect modeling. The output waveform observed at the receiver of the interconnect example is shown in the Figure 14.

SPICE Netlist

The netlists are organized as a group of subcircuits. In each subcircuit model netlist, the model name should be followed by a list of external node interconnects. When copying "SUBCKT" netlist files to your text editor, use Adobe® Acrobat® Reader® 4.0 or higher to ensure proper conversion.

SPICE Parameter Information

In addition to the schematics and netlists there is a listing of the SPICE parameters for the transistors referenced in the schematics and netlists. These parameters represent a typical device of a given transistor. Varying the typical parameters will affect the DC and AC performance of the structures; but for the type of modeling intended by this note, the actual delay times are not necessary and are not modeled, as a result variation of the device parameters are meaningless. The performance levels are more easily varied by other methods and will be discussed in the next section. The resistors referenced in the schematics are polysilicon and have no parasitic capacitance in the real circuit and none is required in the model. The schematics display only the devices needed in the SPICE netlists.

Modeling Information

The bias drivers for the devices are not included as they are unnecessary for interconnect simulations and their use results in a large increase in model complexity and simulation time. The internal reference voltages (V_{BB} , V_{CS} , etc.) should be driven with ideal constant voltage sources. If a GigaComm device is used in positive mode the levels vary one to one with the power supply; but are constant as a function of temperature.

The schematics and SPICE parameters will provide a typical output waveform, which can be seen in Figures 9 and 10. Note that ESD and package models will add 5 ps-7 ps to rise and fall time of the output waveform. Simple adjustments can be made to the models allowing output characteristics to simulate conditions at or near the corners of the data book specifications. Consistent cross-point voltages need to be maintained.

To adjust rise and fall times:

Produce the desired rise and fall times output slew rates by adjusting collector load resistors to change the gates tail current. The V_{CS} voltage will affect the tail current in the output differential, which will interact with the load resistor and collector resistor to determine t_r and t_f at the output.

• To adjust the V_{OH}:

Adjust the V_{OH} and V_{OL} level by the same amount by varying V_{CC} . The output levels will follow changes in V_{CC} at a 1:1 ratio.

ullet To adjust the V_{OL} only:

Adjust the V_{OL} level independently of the V_{OH} level by increasing or decreasing the collector load resistance. Note that the V_{OH} level will also change slightly due to an I_{BASE} R drop across the collector load resistor. The V_{OL} can be changed by varying the V_{CS} supply, and therefore the gate current through the current source resistor.

Device Specifics NBSG16VS

The NBSG16VS is a differential receiver/driver with variable output amplitude which is controlled by a voltage applied to V_{CRTL} over the range of V_{CC} to $V_{CC}-2$ V. These V_{CTRL} voltages produce corresponding output amplitudes over the range of 75 mV to 750 mV (see Data Sheet Figure 11). The SPICE model for NBSG16VS simulates seven selected swings within the output amplitude range by adjusting V_{CS} to one of seven voltages per Table 2. Simulation tr/tf represents the worst case (fastest) edges. A DC offset must be applied to all voltages to convert LVNECL to LVPECL at a 1:1 ratio.

NBSG53A, NBSG72A, and NBSG86A

The NBSG53A, NBSG72A, and NBSG86A are multifunctional differential GigaComm devices with Output Level Select (OLS) capability. The OLS input pin is used to program the peak–to–peak output amplitude between 0 mV and 800 mV in five discrete steps. When simulating output of the NBSG53A, NBSG72A, or NBSG86A, use Table 2, V_{CS} value from line 3, 5, 7, or 10 to obtain desired output amplitude swing.

Table 2. Required V_{CS} for Selected Output Amplitudes of the NBSG16VS

Output Amplitude (mV)		V _{CS} (V)
1.	75	V _{EE} + 0.865
2.	100	V _{EE} + 0.9
3.	200	V _{EE} + 0.98
4.	300	V _{EE} + 1.06
5.	400	V _{EE} + 1.15
6.	500	V _{EE} + 1.23
7.	600	V _{EE} + 1.3
8.	700	V _{EE} + 1.38
9.	750	V _{EE} + 1.42
10.	800	V _{EE} + 1.46

Summary

The information included in this kit provides adequate information to run a SPICE level system interconnect simulation. The block diagram in Figure 3 illustrates a

typical situation, which can be modeled using the information in this kit. Device input or output models are presented in Table 3.

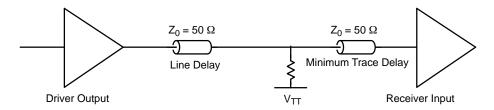


Figure 3. Typical Application for I/O SPICE Modeling Kit

Table 3. GigaComm Input/Output Buffer Selector Guide

Device	Function	Input Model	Output Model
NB7L11M	2.5/3.3 V 1:2 Differential Clock/Data Driver with CML Outputs	SG_INBUF	SG_OBUF_02
NB7L14M	2.5/3.3 V 1:4 Differential Clock/Data Driver with CML Outputs	SG_INBUF	SG_OBUF_02
NB7L86M	2.5/3.3 V Differential Smart Gate with CML Outputs	SG_INBUF	SG_OBUF_02
NBSG11	2.5/3.3 V Differential Clock Driver with RSECL Outputs	SG_INBUF	SG_OBUF_01
NBSG14	2.5/3.3 V Differential Receiver/Driver with RSECL Outputs	SG_INBUF	SG_OBUF_01
NBSG16	2.5/3.3 V Differential Receiver/Driver with RSECL Outputs	SG_INBUF	SG_OBUF_01
NBSG16VS	2.5/3.3 V Differential Receiver/Driver with Variable Output Swing	SG_INBUF	SG_OBUF_01*
NBSG16M	2.5/3.3 V Differential CML Receiver/Driver	SG_INBUF	SG_0BUF_02
NBSG53A	2.5/3.3 V Selectable Differential Clock and Data D Flip-Flop/Clock Divider with Reset and OLS	SG_INBUF	SG_OBUF_01*
NBSG72A	3.5/3.3 V Differential CML 2x2 Crosspoint Switch with OLS	SG_INBUF	SG_OBUF_01*
NBSG86A	2.5/3.3 V Differential Smart Gate with OLS	SG_INBUF	SG_OBUF_01*

^{*}Note: See Device Specifics and Table 2 for Details.

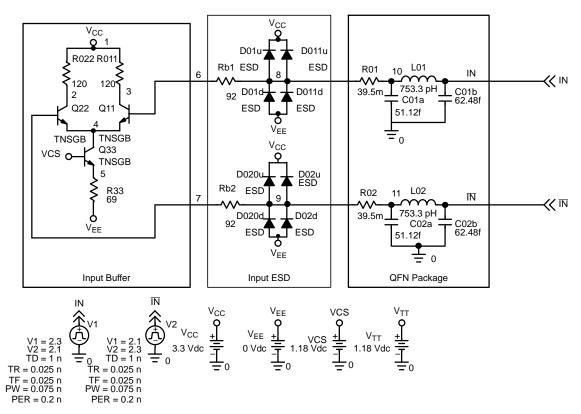


Figure 4. Simplified Input Circuitry - SG_INBUF

```
.SUBCKT SG_INBUF IN INB VCC VEE VCS
Q Q11
             3 6 4 TNSGB
Q_Q22
             2 7 4 TNSGB
Q Q33
             4 VCS 5 TNSGB
R_R011
              3 VCC 120
R R022
              2 VCC 120
R R33
             VEE 5 69
R Rb1
             6 8 92
             9 7 92
R Rb2
             8 10 39.5m
R_R01
             9 11 39.5m
R_R02
             10 IN 753.3pH
L L01
             11 INB 753.3pH
L_L02
D D01d
              VEE 8 ESD
D D011d
               VEE 8 ESD
D D02d
              VEE 9 ESD
D_D020d
               VEE 9 ESD
D D01u
              8 VCC ESD
D_D011u
               8 VCC ESD
D D02u
               9 VCC ESD
D_D020u
               9 VCC ESD
C C01a
              0 10 51.12f
C C02a
              0 11 51.12f
C C01b
              0 IN 62.48f
C C02b
              0 INB 62.48f
             VCC 0 3.3Vdc
V VCC
V VCS
             VCS 0 1.18Vdc
V_VEE
             VEE 0 0Vdc
V V1
            IN 0 PULSE 2.3 2.1 1n 0.025n 0.025n 0.075n 0.2n
V V2
            INB 0 PULSE 2.1 2.3 1n 0.025n 0.025n 0.075n 0.2n
.END SG INBUF
```

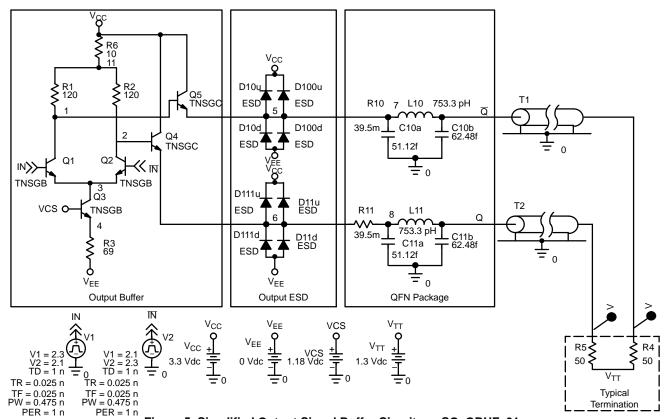


Figure 5. Simplified Output Signal Buffer Circuitry – SG_OBUF_01

.SUBCKT SG_OBUF_01 IN INB VCC VEE VTT VCS Q QB

```
1 IN 3 TNSGB
Q_Q1
             2 INB 3 TNSGB
Q_Q2
             3 VCS 4 TNSGB
Q_Q3
             VCC 2 6 TNSGC
Q_Q4
             VCC 1 5 TNSGC
Q_Q5
R_R1
             1 11 120
R R2
             2 11 120
R R3
             VEE 4 69
R R4
             10 VTT 50
R_R5
             9 VTT 50
R R6
             11 VCC
                    10
R R10
              5 7 39.5m
R R11
              6 8 39.5m
C C10b
               0 QB 62.48f
C_C11a
               0 8 51.12f
C_C11b
C_C10a
               0 Q
                    62.48f
               0 7
                    51.12f
              7 QB 753.3pH
L L10
              8 Q 753.3pH
L_L11
D D111d
                VEE 6 ESD
D D111u
                6 VCC ESD
D D100u
                5 VCC ESD
D D10u
               5 VCC ESD
D_D11u
                6 VCC ESD
D D100d
                VEE 5 ESD
D D10d
               VEE 5 ESD
D D11d
               VEE 6 ESD
V VCC
              VCC 0 3.3Vdc
v_vcs
              VCS 0 1.18Vdc
V VTT
              VTT 0 1.3Vdc
v^-VEE
              VEE 0 0Vdc
V_V1
             IN 0 PULSE 2.3 2.1 1n 0.025n 0.025n 0.075n 0.2n
V_V2
             INB 0 PULSE 2.1 2.3 1n 0.025n 0.025n 0.075n 0.2n
T_T1
             QB 0 10 0 Z0=50 TD=80ps
T T2
             Q 0 9 0 Z0=50 TD=80ps
.END SG_OBUF_01
```

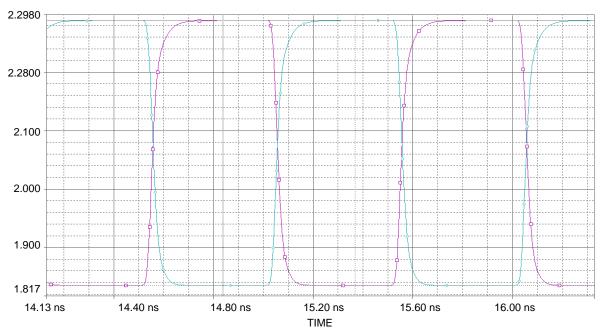


Figure 6. Typical Output Waveform of the SG_OBUF_01 at 1 GHz (tr = 34 ps, tf = 32 ps, Voutpp = 451 mV, Voh = 2.288 V, Vol=1.835 V)

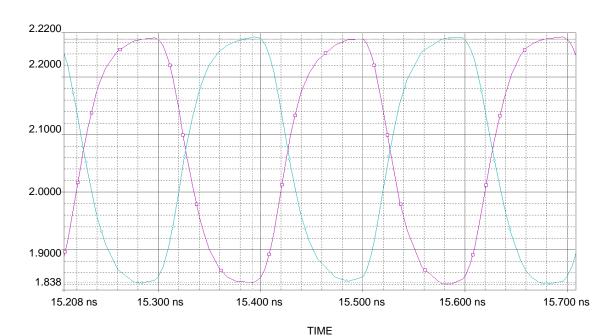


Figure 7. Typical Output Waveform of the SG_OBUF_01 at 5 GHz (tr = 32 ps, tf = 30 ps, Voutpp = 422 mV, Voh = 2.26 V, Vol = 1.84 V)

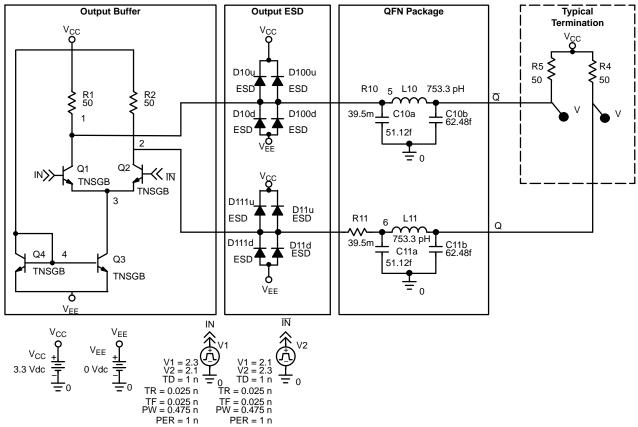


Figure 8. Simplified Output Signal Buffer Circuitry - SG_OBUF_02

```
.SBUCKT SG OBUF02 IN INB VEE VCC VCS Q QB
            1 IN 3 TNSGB
Q_Q1
Q_Q2
            2 INB 3 TNSGB
            3 4 VEE TNSGB
Q_Q3
            4 4 VEE TNSGB
Q_Q4
            1 VCC 50
R_R1
R R2
            2 VCC 50
R R3
            QB VCC 50
R R4
            Q VCC 50
R R10
             1 5 39.5m
             2 6 39.5m
R R11
             5 QB 753.3pH
L L10
              6 Q 753.3pH
L L11
C C10b
              0 QB 62.48f
C C10a
              0 5 51.12f
C C11a
              0 6 51.12f
C C11b
              0 Q 62.48f
D D10d
              VEE 1 ESD
D D11d
              VEE 2 ESD
               2 VCC ESD
D D111u
D_D111d
               VEE 2 ESD
               1 VCC ESD
D D100u
D_D10u
              1 VCC ESD
D D11u
               2 VCC ESD
D D100d
               VEE 1 ESD
V_VEE
              VEE 0 0Vdc
V_VCC
             VCC 0 3.3Vdc
I_I1
            VCC 4 DC 16mAdc
V_V1
             IN 0 PULSE 2.3 2.1 1n 0.025n 0.025n 0.475n 1n
V_V2
             INB 0 PULSE 2.1 2.3 1n 0.025n 0.025n 0.475n 1n
.END SG_OBUF02
```

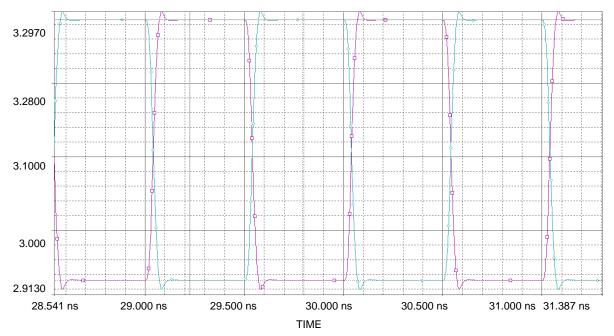


Figure 9. Typical Output Waveform of the SG_OBUF_02 at 1 GHz (tr = 30 ps, tf = 28 ps, Voutpp = 354 mV, Voh = 3.29 V, Vol = 2.93 V)

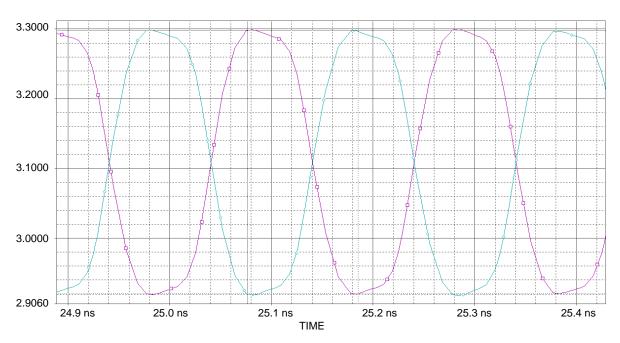


Figure 10. Typical Output Waveform of the SG_OBUF_02 at 5 GHz (tr = 29 ps, tf = 28 ps, Voutpp = 364 mV, Voh = 3.29 V, Vol = 2.92 V)

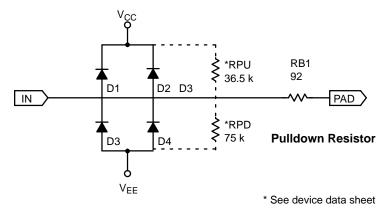


Figure 11. Input ESD

.SUBCKT	IN_ESD	VCC VEE	IN PAD
D1	IN	VCC	ESD
D2	IN	VCC	ESD
D3	VEE	IN	ESD
D4	VEE	IN	ESD
RPD	IN	VEE	75K
RPU	IN	VCC	36.5K
RB1	IN	PAD	92
TITE C TI	. ECD		

.ENDS IN ESD

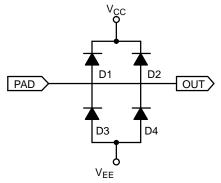


Figure 12. Output ESD

.SUBCK	T OUT_	ESD VCC	VEE	OUT
D1	OUT	VC	CC	ESD
D2	OUT	VC	CC	ESD
D3	VEE	OUT		ESD
D4	VEE	OUT		ESD
.ENDS	OUT_ES	D		

*********Transistor and Diod Models for GigaComm***************

.MODEL TNSGC NPN (IS=1.47e-16 BF=180 NF=1 VAF=96.3 IKF=1.62e-01 ISE=2.96e-15 NE=2.5 BR=20.2 VAR=2.76 IKR=1.34e-02 ISC=2.14e-16 NC=1.426 RB=25 IRB=1.50e-03 RBM=4 RE=1 RC=7 CJE=3.34e-15 VJE=.8867 MJE=.2868 TF=2.00e-12 ITF=0.25e-01 XTF=0.7 VTF=0.35 PTF=20 TR=0.5e-9 CJC=1.08e-15 VJC=0.632 MJC=0.301 XCJC=.3 CJS=8.12e-16 VJS=.4193 MJS=0.256 EG=1.119 XTI=3.999 XTB=0.8826 FC=0.9)

.MODEL TNSGB NPN (IS=2.18e-17 BF=179 NF=1 VAF=96.5 IKF=2.42e-02 ISE=3.83e-16 NE=2.5 BR=20.4 VAR=2.76 IKR=1.98e-03 ISC=2.91e-17 NC=1.426 RB=55 IRB=1.12e-04 RBM=48 RE=6 RC=11 CJE=4.98e-16 VJE=.8867 MJE=.2868 TF=2.00e-12 ITF=0.4e-02 XTF=0.7 VTF=0.6 PTF=20 TR=0.5e-9 CJC=1.55e-16 VJC=0.632 MJC=0.301 XCJC=0.3 CJS=1.71e-16 VJS=.4193 MJS=0.256 EG=1.119 XTI=3.999 XTB=0.8826 FC=0.9)

.MODEL ESD D (IS=9.99E-21 CJO=65.2E-15 RS=50.1 VJ=0.82 M=0.25 BV= 35)

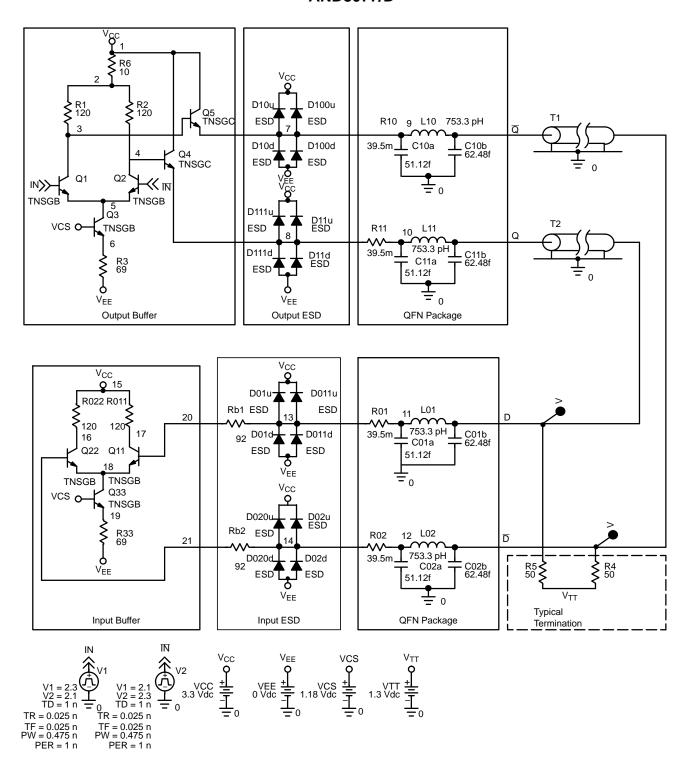


Figure 13. Example of the Typical Interconnect Circuit

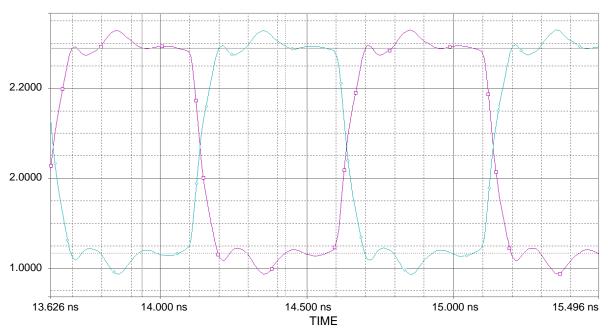


Figure 14. Output Waveform of the Interconnect Example Shown in Figure 13 (Frequency = 1 GHz, tr = 49 ps, tf = 53 ps, Voutpp = 455 mV)

```
* Package: 16 pin QFN
* Model for 16 pins
* Note:
* 1. The model assumes ground plane is 15 mil below package
* 2. The model assumes flag is grounded
\star 3. The model is based on GigaComm device 1.475mm x 1.475mm
* 4. Wire bond parasitics are lumped with lead frame post.
* 5. Lump element equivalent model valid up to 10 Ghz
*****************
* Lead Frame drawing: ASAT 3mm x 3mm QFN
* Case Outline:
* LC file : 16qfn3x3.LC
******************
* Package: GigaComm 16 pin 3mm x 3mm QFN
* Model for 16 pins
* Conductor number-pin designation cross reference:
   Conductor
              Pin
      1
                 1
      2
      3
                3
      4
      5
                 5
      6
      7
                 7
      8
                 8
      9
                 9
     10
                10
     11
                11
     12
               12
     13
               13
     14
               14
     15
                15
      16
                16
* number of lumps: 1
* COMPRESSION OF SUBCIRCUITS PERFORMED: discard ratio is 0.050
.SUBCKT PACKAGE N011 N010 N021 N020 N031 N030 N041 N040
+ N05I N05O N06I N06O N07I N07O N08I N08O N09I N09O
+ N10I N100 N11I N110 N12I N120 N13I N130 N14I N140
+ N15I N15O N16I N16O BD GND
R01
    N01I N01C 4.300e-02
C01a N01C BD_GND 6.674e-14
C01b N010 BD_GND 8.157e-14
L01 N01C N01O 8.418e-10
R02 N02I N02 3.950e-02
C02a N02C BD GND 5.153e-14
C02b N02O BD GND 6.298e-14
L02 N02C N02O 7.557e-10
R03 N03I N03C 3.950e-02
C03a N03C BD GND 5.364e-14
     N030 BD_GND 6.556e-14
C03b
           N030 7.550e-10
    N03C
L03
     N04I
            N04C 4.300e-02
R04
           BD GND 6.687e-14
C04a
    N04C
C04b
     N040
            BD GND
                    8.173e-14
```

L04	N04C	N040	8.427e-10
R05	N05I	N05C	4.300e-02
C05a	N05C	BD GND	6.633e-14
C05b	N050	_	8.107e-14
L05	N05C	N050	
R06	N06I	N06C	3.950e-02
C06a	N06C	BD GND	5.202e-14
C06b	N060		6.358e-14
L06	N06C	N060	
R07	N07I	N07C	3.950e-02
C07a	N07C	BD GND	
C07b	N070	BD GND	6.408e-14
L07	N07C	_	7.551e-10
R08	NO8I	N08C	
C08a	N08C		6.682e-14
C08b	N080		8.168e-14
L08	N08C	N080	8.432e-10
R09	N09I	N09C	4.300e-02
C09a	N09C	BD GND	
C09b		_	8.074e-14
L09	N09C	_	8.418e-10
R10	N10I	N10C	3.950e-02
C10a	N10C	BD_GND	
C10b	N100	BD GND	6.248e-14
L10	N10C	_	7.533e-10
R11	N11I	N11C	3.950e-02
C11a	N11C		5.166e-14
C11b	N110	BD_GND	6.314e-14
L11	N11C	N110	7.524e-10
R12	N12I	N12C	4.300e-02
C12a	N12C		6.786e-14
C12b	N120	_	8.294e-14
L12	N12C	N120	8.415e-10
R13	N13I	N13C	4.300e-02
C13a	N13C	BD GND	
C13b	N130	_	8.101e-14
L13	N13C	_	8.426e-10
R14	777N14I	N14C	3 950e-02
C14a	N14C	BD GND	3.950e-02 5.238e-14 6.402e-14
C14b	N140	BD_GND	6 402e-14
L14	N14C	N140	
			3.950e-02
C15a	N15C		
C15b	N150	BD_GND BD GND	
	N15C	N150	7.514e-10
	N16I	N16C	
	N16C		6.692e-14
		_	8.179e-14
		_	8.412e-10
L16 K0102		L02	0.1711
C0102a		N02C	1.740e-14
	NOIC		2.126e-14
K0103		L03	0.0549
K0115 K0116	L01 L01	L15 L16	0.0549
		N16C	
C0116a	MOTO	MITOC	4.797e-15 5.863e-15
	L02		
			1.622e-14
C0203b			1.983e-14 0.0690
K0204	L02		
K0216	L02	пΤρ	0.0555

K0304	L03	L04	0.1713
C0304a	N03C	N04C	1.744e-14
C0304b	N030	N040	2.131e-14
K0305	L03	L05	0.0563
K0405	L04	L05	0.1098
C0405a	N04C	N05C	4.747e-15
C0405b	N040	N050	5.803e-15
K0406	L04	L06	0.0560
K0506		L06	0.1723
C0506a	N05C	N06C	1.739e-14
C0506b	N050	N060	2.125e-14
K0507	L05	L07	0.0695
K0607	L06	L07	0.1578
C0607a	N06C	N07C	1.633e-14
C0607b	N060		1.996e-14
K0608	L06	L08	0.0676
K0708	L07	L08	0.1708
C0708a	N07C	N08C	1.748e-14
C0708b			2.136e-14
K0709	L07	L09	0.0551
K0809	L08	L09	0.1085
C0809a	N08C	N09C	4.797e-15
C0809b	N080	N090	5.863e-15
K0810		L10	
K0910	L09	L10	
C0910a	N09C	N10C	1.734e-14
C0910b	N090	N100	
K0911	L09	L11	0.0684
K1011	L10		0.1574
C1011a	N10C	N11C	1.613e-14
C1011b			1.972e-14
K1012	L10	L12	0.0673
K1112	L11	L12	0.1711
C1112a	N11C	N12C	1.751e-14
C1112b	N110		2.139e-14
K1113	L11	L13	0.0558
K1213	L12		0.1097
C1213a	N12C	N13C	4.797e-15
C1213b	N120	N130	5.863e-15
K1214		L14	0.0561
K1314	L13	L14	0.1715
C1314a	N13C	N14C	1.748e-14
C1314b	N130	N140	
K1315	L13	L15	0.0678
K1415	L14	L15	0.1573
C1415a	N14C	N15C	1.636e-14
C1415b	N140	N150	
K1416	L14	L16	0.0682
K1516	L15	L16	0.1707
C1516a	N15C	N16C	1.748e-14
C1516b		N160	2.137e-14
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